

## **INCHANGE SEMICONDUCTOR**

isc N-Channel MOSFET Transistor TK3R3E

## TK3R3E03GL, ITK3R3E03GL

## • FEATURES

- Low drain-source on-resistance: R⊳s(on) ≤3.3mΩ.
- Enhancement mode:

Vth =1.3 to 2.3V (V<sub>DS</sub> = 10 V, I<sub>D</sub>=0.5mA)

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## DESCRITION

Switching Voltage Regulators

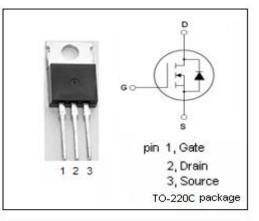
#### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

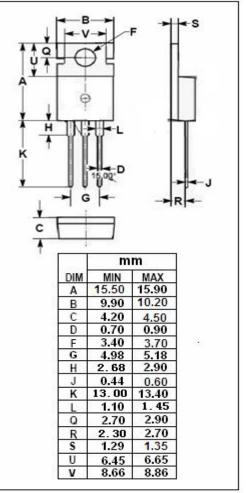
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>DSS</sub>	Drain-Source Voltage	30	V				
V <sub>GS</sub>	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous	80	А				
I <sub>DM</sub>	Drain Current-Single Pulsed	360	A				
PD	Total Dissipation @Tc=25°C	104	W				
Tj	Max. Operating Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature	-55~150	°C				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT		
Rth(ch-c)	Channel-to-case thermal resistance	1.2	°C <b>/W</b>		
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C/W		

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# isc N-Channel MOSFET Transistor TK3R3E03GL, ITK3R3E03GL

### **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =10mA	30			v
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =10V; I <sub>D</sub> =0.5mA	1.3		2.3	v
$R_{\text{DS(on)}}$	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =40A			3.3	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V; V <sub>GS</sub> = 0V			10	μA
VSDF	Diode forward voltage	I <sub>DR</sub> =80A, V <sub>GS</sub> = 0 V			1.2	v

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